CLAIMS

1. A method for producing a single crystal, comprising supplying a vapor gas from silicon carbide as a raw material to a seed crystal formed of a silicon carbide single crystal to grow the seed crystal, wherein the seed crystal is disposed in a part of crystal growth, with a crystal face of the seed crystal inclined relative to a (0001) plane or (000-1) plane, thereby making crystal growth.

2. A method for producing a single crystal, comprising supplying a vapor gas from silicon carbide as a raw material to a seed crystal formed of a silicon carbide single crystal to grow the seed crystal, wherein the seed crystal is disposed in a low-temperature region of a part of crystal growth, with a crystal face of the seed crystal inclined relative to a (0001) plane or (000-1) plane, thereby making the crystal growth at a crystal growth rate of 0.05 mm/hr or less during an initial stage of crystal growth and at a crystal growth rate of 1 mm/hr or less thereafter.

3. A method according to claim 1 or claim 2, wherein the crystal face of the seed crystal is inclined by 4 to 45° relative to the (0001) plane or (000-1) plane.

4. A method according to any one of claims 1 to 3, wherein the seed crystal is a seed crystal comprising a silicon carbide single crystal cut, polished, then washed and subjected to sacrificial oxidation, and surface-treated by HF washing.

5. A silicon carbide seed crystal comprising a silicon carbide single crystal cut, polished, then subjected to washing treatment and surface-treated, and having a crystal face inclined relative to a (0001) plane or (000-1) plane.

6. A silicon carbide seed crystal according to claim 5, wherein the crystal face is inclined by 4 to 45° relative to the (0001) plane or (000-1) plane.

7. A silicon carbide single crystal that is grown using a silicon carbide seed crystal having a crystal face inclined by 4 to 45° relative to the (0001) plane or (000-1) plane.